

Silicon PNP Darlington Power Transistors

2SB1587

DESCRIPTION

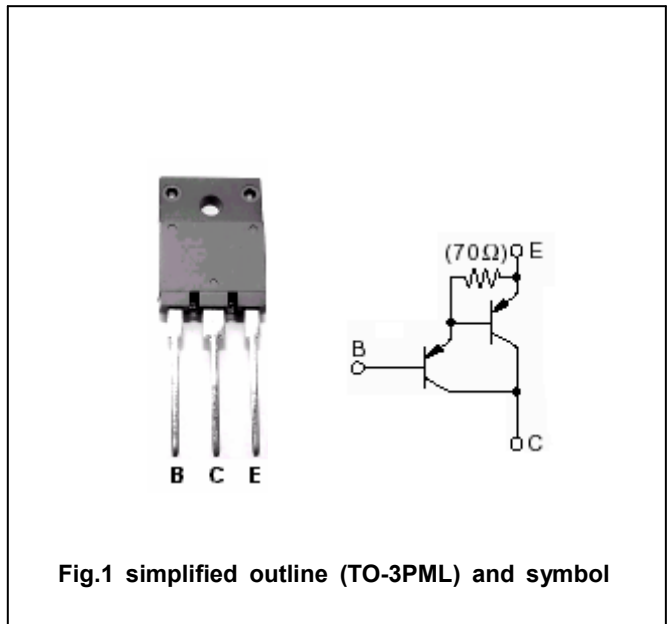
- With TO-3PML package
- Complement to type 2SD2438

APPLICATIONS

- Audio, Series Regulator and General Purpose

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

Absolute maximum ratings($T_c=25^\circ$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-160	V
V_{CEO}	Collector-emitter voltage	Open base	-150	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current		-8	A
I_B	Base current		-1	A
P_C	Collector power dissipation	$T_c=25^\circ$	75	W
T_j	Junction temperature		150	$^\circ$
T_{stg}	Storage temperature		-55~150	$^\circ$

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-30mA; I _B =0	-150			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-6 A; I _B =-6m A			-2.5	V
V _{BEsat}	Base-emitter saturation voltage	I _C =-6 A; I _B =-6m A			-3.0	V
I _{CBO}	Collector cut-off current	V _{CB} =-160V; I _E =0			-100	μA
I _{EBO}	Emitter cut-off current	V _{EB} =-5V; I _C =0			-100	μA
h _{FE}	DC current gain	I _C =-6A ; V _{CE} =-4V	5000			
f _T	Transition frequency	I _C =-1A ; V _{CE} =-12V		65		MHz
C _{OB}	Output capacitance	I _E =0; V _{CB} =-10V; f=1MHz		160		pF

Switching times

t _{on}	Turn-on time	I _C =-6A; R _L =10Ω I _{B1} =-I _{B2} =-6mA V _{CC} =-60V		0.7		μs
t _s	Storage time			3.6		μs
t _f	Fall time			0.9		μs

◆ h_{FE} classifications

O	P	Y
5000-12000	6500-20000	15000-30000

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PACKAGE OUTLINE

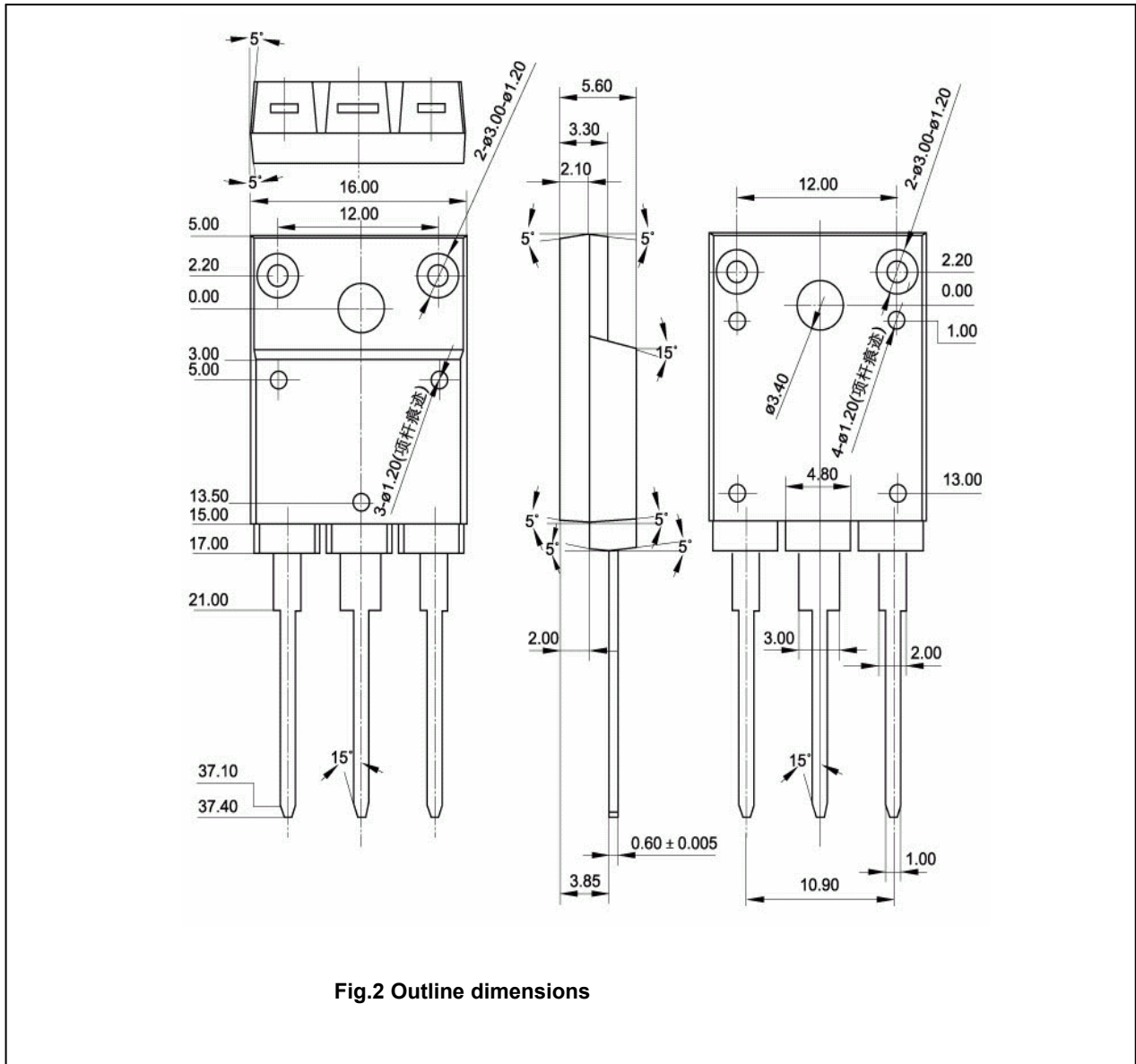


Fig.2 Outline dimensions